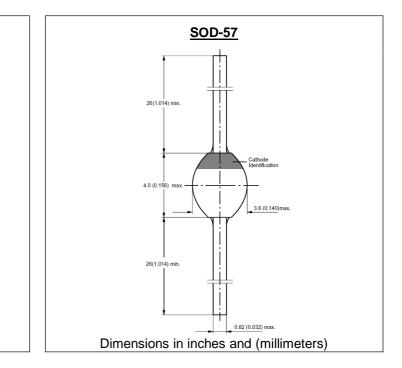
SF1600

SINTERED GLASS JUNCTION ULTRAFAST AVALANCHE RECTIFIER VOLTAGE: 1600V CURRENT: 1.0A



Very low switching losses Glass passivated Low reverse current High reverse voltage Hermetically sealed package





MECHANICAL DATA

Case: SOD-57 sintered glass case Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C Polarity: color band denotes cathode end Mounting position: any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	SF1600	unit
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	1600	V
Maximum RMS Voltage	V _{RMS}	1120	V
Maximum DC blocking Voltage	V _{DC}	1600	V
Minimum Reverse Breakdown Voltage IR = 100μA	V _{(BR)R}	1650	V
Average Forward Rectified Current half- sinewave, Rth(ja)=45K/W, Ta=25°C	I _{FAV}	1.0	A
Peak Forward Surge Current at tp=10ms, half sinewave	I _{FSM}	30	A
Maximum Forward Voltage at 1.0A	V _F	3.4	V
Non-repetitive peak reverse avalanche energy at I _{BR(R)} =0.4A	E _R	10	mJ
Maximum DC Reverse CurrentTa = 25° Cat rated DC blocking voltageTa = 125° C	I _R	5.0 50.0	μΑ
Maximum Reverse Recovery Time (Note 1)	Trr	75	nS
Typical Thermal Resistance (Note 2)	Rth(ja)	45	K/V
Storage and Operating Junction Temperature	Tstg, Tj	-55 to +175	°C

1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A 2. Lead length I =10mm, T_L = constant

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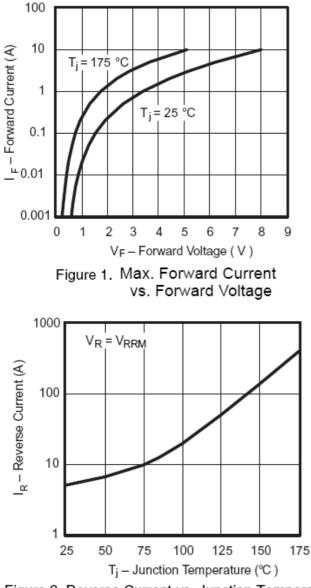


Figure 3. Reverse Current vs. Junction Temperature

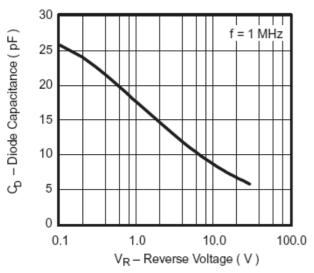
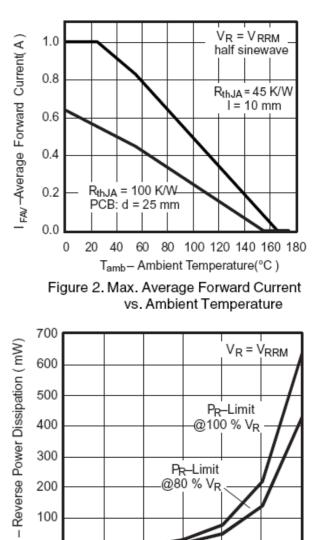


Figure 5. Diode Capacitance vs. Reverse Voltage



100

0

25

50

75

100

Figure 4. Max. Reverse Power Dissipation vs.

Junction Temperature

Ti - Junction Temperature (°C)

125

150

175

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